L Numb r	Hits	S arch T xt	DB	Tim stamp
•	7338	pixel ADJ electr de	USPAT;	2001/07/02
			EPO; JPO	20:55
,	22931	thin ADJ film ADJ transistor r TFT	USPAT;	2001/07/02
			EPO; JPO	20:56
	48082	storage ADJ capacit\$4	USPAT;	2001/07/02
			EPO; JPO	20:57
-	1135	metallic ADJ pattern	USPAT;	2001/07/02
			EPO; JPO	20:58
-	4557	(pixel ADJ electrode) and (thin ADJ film ADJ	USPAT;	2001/07/02
		transistor or TFT)	EPO; JPO	20:58
-	699	(storage ADJ capacit\$4) and ((pixel ADJ	USPAT;	2001/07/02
		electrode) and (thin ADJ film ADJ transistor or TFT))	EPO; JPO	20:58
,	0	(metallic ADJ pattern) and ((storage ADJ	USPAT;	2001/07/02
		capacit\$4) and ((pixel ADJ electrode) and	EPO; JPO	20:59
		(thin ADJ film ADJ transistor or TFT)))	1	
•	17508	wiring ADJ pattern	USPAT;	2001/07/02
	:	-	EPO; JPO	21:00
	28	(wiring ADJ pattern) and ((storage ADJ	USPAT;	2001/07/05
		capacit\$4) and ((pixel ADJ electrode) and	EPO; JPO	12:04
		(thin ADJ film ADJ transistor or TFT)))		
•	4	eletrode ADJ pattern	USPAT;	2001/07/02
		•	EPO; JPO	21:03
-	9840	electrode ADJ pattern	USPAT;	2001/07/02
		-	EPO; JPO	21:04
-	50	drain ADJ electrode ADJ pattern	USPAT;	2001/07/02
		•	EPO; JPO	21:05
	50	storage ADJ electrode ADJ pattern	USPAT;	2001/07/05
		-	EPO; JPO	12:08
	0	(drain ADJ electrode ADJ pattern) and	USPAT;	2001/07/02
		(storage ADJ electrode ADJ pattern)	EPO; JPO	21:05
-	100	(drain ADJ electrode ADJ pattern) or	USPAT;	2001/07/02
		(storage ADJ electrode ADJ pattern)	EPO; JPO	21:06
	27943	contact ADJ hole	USPAT;	2001/07/02
			EPO; JPO	21:07
	5	(drain ADJ electrode ADJ pattern) and	USPAT;	2001/07/02
	-	(contact ADJ hole)	EPO; JPO	21:12
	1	("5708483").PN.	USPAT;	2001/07/02
	_	•	EPO; JPO	21:13
	2	("5737049").PN.	USPAT;	2001/07/02
	_	, ,	EPO; JPO	21:14
	2	("5435324").PN.	USPAT;	2001/07/02
	_	,	EPO; JPO	21:14
	41	(storage ADJ electrode ADJ pattern) and	USPAT;	2001/07/05
	• •	(contact ADJ hole)	EPO; JPO	12:19
	0	storage ADJ electrode ADJ pattern with	USPAT;	2001/07/03
		(periph ry r annular)	EP ; JPO	08:13
	50	storage ADJ electrod ADJ pattern	USPAT;	
	30	ororage and election. And pattern	EPO; JPO	2001/07/03
	41	(st_rage ADJ_lectrode ADJ pattern) and	·	08:16
	7.	for rade who rections who hattern) and	USPAT;	2001/07/03

-	0	((st rage ADJ lectr d ADJ patt rn) and	USPAT;	2001/07/03
		(c ntact ADJ h le)) and pixel	EPO; JPO	08:19
•	0	(st rag ADJ electr d ADJ pattern) and	USPAT;	2001/07/03
		pixel	EPO; JPO	08:19
-	0	(storage ADJ electr de ADJ pattern) and	USPAT;	2001/07/03
		TFT	EPO; JPO	08:20
	618	(electrode ADJ pattern) and (contact ADJ	USPAT;	2001/07/03
		hole)	EPO; JPO	08:22
-	138	((electrode ADJ pattern) and (contact ADJ	USPAT;	2001/07/03
		hole)) and pixel	EPO; JPO	08:22
•	93	(((electrode ADJ pattern) and (contact ADJ	USPAT;	2001/07/03
		hole)) and pixel) and TFT	EPO; JPO	08:22
•	3	((((electrode ADJ pattern) and (contact ADJ	USPAT;	2001/07/03
		hole)) and pixel) and TFT) and storage ADJ electrode	EPO; JPO	16:34
•	1	((((electrode ADJ pattern) and (contact ADJ	USPAT;	2001/07/03
		hole)) and pixel) and TFT) and drain ADJ	EPO; JPO	13:05
		electrode ADJ pattern	,	
-	64	((((electrode ADJ pattern) and (contact ADJ	USPAT;	2001/07/03
		hole)) and pixel) and TFT) and drain ADJ	EPO; JPO	08:58
		electrode		
-	0	(((((electrode ADJ pattern) and (contact ADJ	USPAT;	2001/07/03
		hole)) and pixel) and TFT) and drain ADJ	EPO; JPO	08:40
		electrode) and (peripher\$4 or annular) ADJ	,	
		pattern		
-	7	(peripher\$4 or annular) ADJ storage ADJ	USPAT;	2001/07/03
		electrode	EPO; JPO	09:01
•	15	(peripher\$4 or annular) ADJ drain ADJ	USPAT;	2001/07/03
		electrode	EPO; JPO	09:58
-	28	((((electrode ADJ pattern) and (contact ADJ	USPAT;	2001/07/03
		hole)) and pixel) and TFT) and (driving with peripher\$4 or annular)	EPO; JPO	13:34
	466	storage ADJ electrode with contact ADJ	USPAT;	2001/07/03
		hole	EPO; JPO	11:24
	1	(storage ADJ electrode with contact ADJ	USPAT;	2001/07/03
		hole) and ((((electrode ADJ pattern) and	EPO; JPO	11:24
		(contact ADJ hole)) and pixel) and TFT)		
-	573	driving ADJ pattern	USPAT;	2001/07/03
			EPO; JPO	13:06
•	573	driving ADJ pattern	USPAT;	2001/07/03
			EPO; JPO	13:08
•	0	((((electrode ADJ pattern) and (contact ADJ	USPAT;	2001/07/03
		hole)) and pixel) and TFT) and (driving ADJ	EPO; JPO	13:08
		pattern)		
-	0	annular ADJ (driving ADJ pattern)	USPAT;	2001/07/03
			EPO; JPO	13:09
-	0	peripher\$4 ADJ (driving ADJ pattern)	USPAT;	2001/07/03
			EPO; JPO	13:09
-	9	((((electr d ADJ pattern) and (c ntact ADJ	USPAT;	2001/07/03
		h le)) and pixel) and TFT) and (peripher\$4	EPO; JPO	13:59
		r annular) ADJ driving		
•	0	(peripher\$4 r annular) ADJ driving ADJ	USPAT;	2001/07/03
		layer	EPO; JPO	14:00

-	1	(p ripher\$4 r annular) ADJ driving ADJ	USPAT;	2001/07/03
		(layer rwir)	EPO; JPO	14:01
-	1052	s urc ADJ electrod with ntact ADJ hole	USPAT;	2001/07/03
			EPO; JPO	16:36
-	389	(source ADJ ctrode with c ntact ADJ	USPAT;	2001/07/03
		hole) and pix 1	EPO; JPO	16:37
-	144	(source ADJ electrode with contact ADJ	USPAT;	2001/07/03
		hole) with pixel ADJ electrode	EPO; JPO	16:38
-	1	((source ADJ electrode with contact ADJ	USPAT;	2001/07/03
		hole) with pixel ADJ electrode) and drain	EPO; JPO	16:39
		ADJ electrode ADJ pattern		
-	34	((storage ADJ capacit\$4) and ((pixel ADJ	USPAT;	2001/07/05
		electrode) and (thin ADJ film ADJ transistor	EPO; JPO	11:36
		or TFT))) and (electrode ADJ pattern)		
	7	storage ADJ electrode ADJ pattern with	USPAT;	2001/07/05
		contact ADJ hole	EPO; JPO	12:09
	466	storage ADJ electrode with contact ADJ	USPAT;	2001/07/05
		hole	EPO; JPO	11:48
-	17	(storage ADJ electrode with contact ADJ	USPAT;	2001/07/05
		hole) and pixel	EPO; JPO	11:48
	0	storage ADJ electrode ADJ pattern with	USPAT;	2001/07/05
		pixel	EPO; JPO	12:08
-	0	storage ADJ electrode ADJ pattern and pixel	USPAT;	2001/07/05
		•	EPO; JPO	12:09
-	66	storage ADJ electrode with pixel	USPAT;	2001/07/05
		-	EPO; JPO	12:10
	1	(storage ADJ capacit\$4 ADJ pattern) and	USPAT;	2001/07/05
		(contact ADJ hole)	EPO; JPO	12:20
	0	(storage ADJ capacit\$4 ADJ pattern) with	USPAT;	2001/07/05
		pixel	EPO; JPO	12:20
	2	(storage ADJ capacit\$4 ADJ pattern) and	USPAT:	2001/07/05
		pixel	EPO; JPO	12:21